



BSS84V

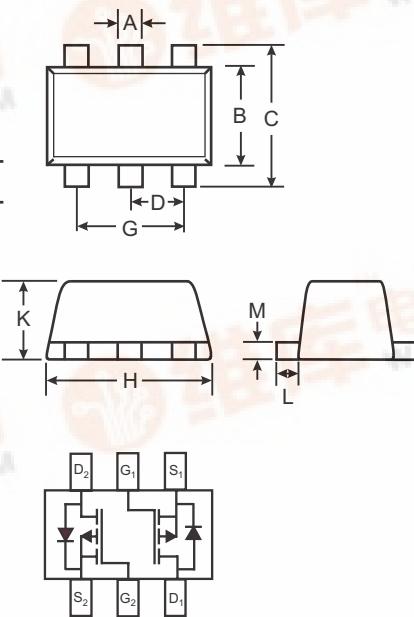
DUAL P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead Free By Design/RoHS Compliant (Note 3)
- "Green" Device (Note 4)

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Code (See Page 2): K84
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approx.)



SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.25
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	0.50		
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.56	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	—

All Dimensions in mm

Maximum Ratings

• $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	-50	V
Drain-Gate Voltage (Note 1)	V_{DGR}	-50	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current (Note 2)	I_D	-130	mA
Total Power Dissipation (Note 2)	P_d	150	mW
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	833	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

Note:

1. $R_{GS} \leq 20\text{K}\Omega$.
2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
3. No purposefully added lead.
4. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics

@ $T_A = 25^\circ\text{C}$ unless otherwise specified

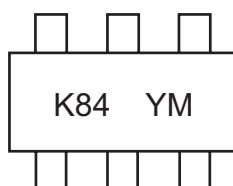
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	-50	-75	—	V	$V_{\text{GS}} = 0\text{V}$, $I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-15 -60 -100	μA μA nA	$V_{\text{DS}} = -50\text{V}$, $V_{\text{GS}} = 0\text{V}$, $T_J = 25^\circ\text{C}$ $V_{\text{DS}} = -50\text{V}$, $V_{\text{GS}} = 0\text{V}$, $T_J = 125^\circ\text{C}$ $V_{\text{DS}} = -25\text{V}$, $V_{\text{GS}} = 0\text{V}$, $T_J = 25^\circ\text{C}$
Gate-Body Leakage	I_{GSS}	—	—	± 50	nA	$V_{\text{GS}} = \pm 20\text{V}$, $V_{\text{DS}} = 0\text{V}$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	-0.8	-1.6	-2.0	V	$V_{\text{DS}} = V_{\text{GS}}$, $I_D = -1\text{mA}$
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	—	2	10	Ω	$V_{\text{GS}} = -5\text{V}$, $I_D = -0.100\text{A}$
Forward Transconductance	g_{FS}	0.05	—	—	S	$V_{\text{DS}} = -25\text{V}$, $I_D = -0.1\text{A}$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	45	pF	$V_{\text{DS}} = -25\text{V}$, $V_{\text{GS}} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{\text{D}(\text{ON})}$	—	10	—	ns	$V_{\text{DD}} = -30\text{V}$, $I_D = -0.27\text{A}$, $R_{\text{GEN}} = 50\Omega$, $V_{\text{GS}} = -10\text{V}$
Turn-Off Delay Time	$t_{\text{D}(\text{OFF})}$	—	18	—	ns	

Ordering Information (Note 6)

Device	Packaging	Shipping
BSS84V-7	SOT-563	3000/Tape & Reel

Notes: 5. Short duration test pulse used to minimize self-heating effect.
6. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information (Note 7)



K84 = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: S = 2005
M = Month ex: 9 = September

Notes: 7. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

Date Code Key

Year							2005	2006	2007	2008	2009	
Code							S	T	U	V	W	
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

DIODES
INCORPORATED

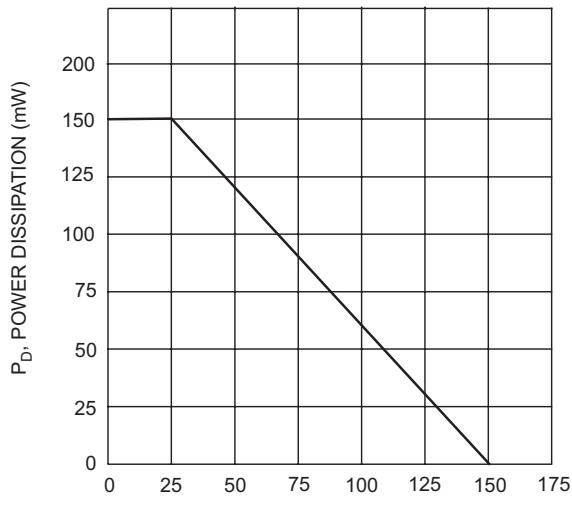


Fig. 1 Max Power Dissipation vs.
Ambient Temperature

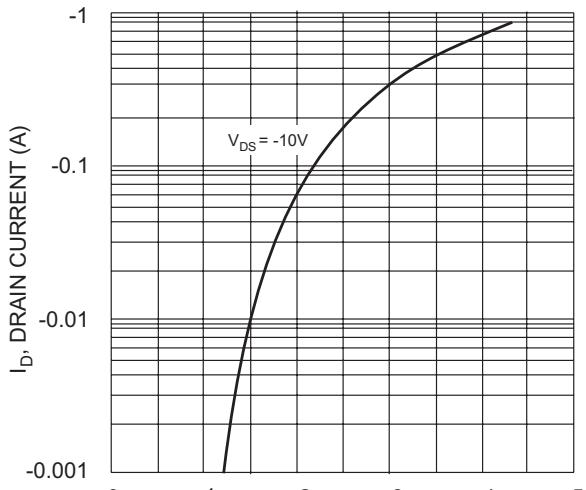


Fig. 3 Typical Transfer Characteristics

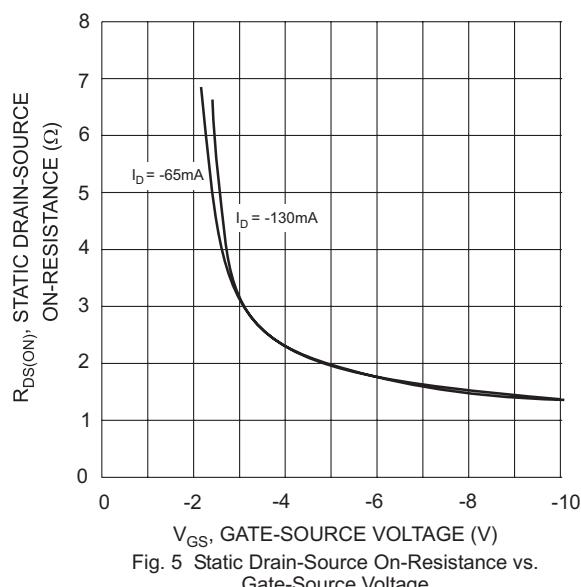


Fig. 5 Static Drain-Source On-Resistance vs.
Gate-Source Voltage

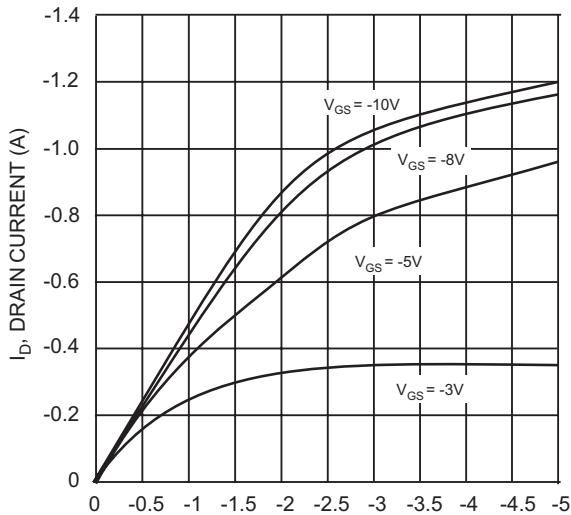


Fig. 2 Typical Output Characteristics

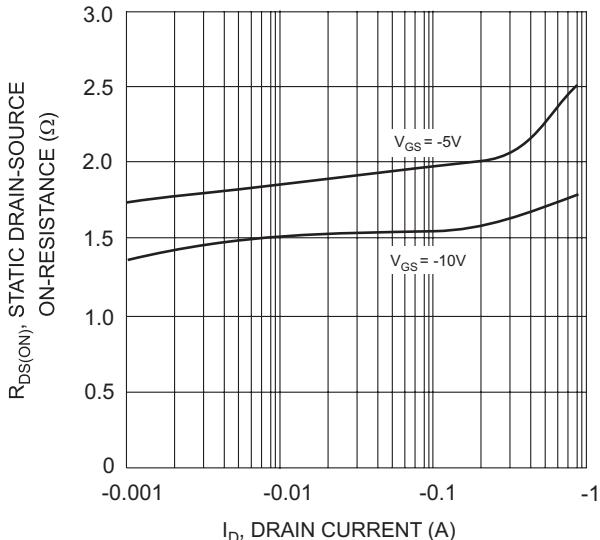


Fig. 4 Static Drain-Source On-Resistance
vs. Drain Current

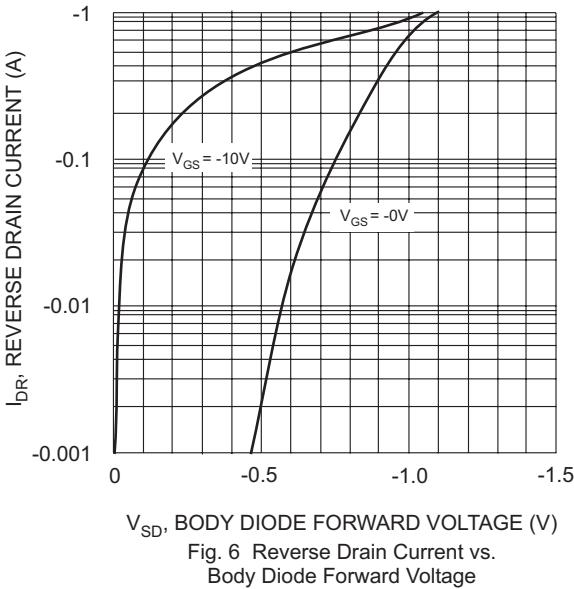


Fig. 6 Reverse Drain Current vs.
Body Diode Forward Voltage



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